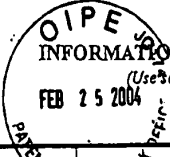



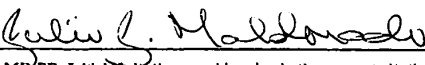


<div style="text-align: center;">  <p>INFORMATION DISCLOSURE CITATION (Use several sheets if necessary) FEB 25 2004</p> </div>		Docket Number (Optional) OKI.227		Application Number NEW	
		Applicant(s) Norio HIRASHITA et al.			
		Filing Date APRIL 5, 2001		Group Art Unit TO BE REASSIGNED	
		<div style="text-align: center;"> OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.) </div>			
<small>*EXAMINER INITIAL</small> 	A	Deep sub-0.1 um MOSFET's with Very Thin SOL Layer for Ultra-Low Power Applicants, Information and Communication Engineers C-II Vol. J81-C-II No. 3, pp. 313-319, August 1998.			
	B	Optimization of Series Resistance in Sub-0.2 um SOI MOSFET's, IEEE Electron Device letters, VOL. 15, No. 9, September 1994, p. 363-365.			
	C	Optimization of series resistance in Sub-0.2 um SOI MOSFET's, 1993 IEEE, pp. IEDM93-723-726-IEDM 93.			
EXAMINER 		DATE CONSIDERED 05/07/2004			
<small>*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance or not considered. Include copy of this form with next communication to applicant.</small>					

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